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| LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) | | | | APPLICANT Klaus Florian Schuegraf et al. | | | |
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| U.S. PATENT DOCUMENTS | | | | | | | |
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| | | | | | | | Yes No |
| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
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| Ron Pompey | | | | 4-2304 | | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |

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